AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A liquid crystal display device comprising:

a pair of substrates;

a liquid crystal interposed between the pair of substrates;

a thin film transistor over one of the pair of substrates; and

a pixel electrode connected to the thin film transistor,

wherein the thin film transistor comprises:

a gate electrode formed over the one of the pair of substrates by fusing conductive nanoparticles,

a first layer including at least one of silicon nitride and ~~nitride oxide~~ silicon nitride oxide formed on and in direct contact with the gate electrode,

a gate insulating layer at least ~~containing~~ comprising a second layer ~~comprising~~ including silicon oxide over the first layer, and

a semiconductor layer over the gate insulating layer.

2. (Currently amended) A liquid crystal display device comprising:

a pair of substrates;

a liquid crystal interposed between the pair of substrates;

a thin film transistor over one of the pair of substrates; and

a pixel electrode connected to the thin film transistor,

wherein the thin film transistor comprises:

a gate electrode formed over the one of the pair of substrates by fusing conductive nanoparticles,

a first layer including at least one of silicon nitride and silicon ~~oxynitride~~ nitride oxide formed on and in direct contact with the gate electrode,

a gate insulating layer at least ~~containing~~ comprising a second layer including [[a]] silicon oxide [[layer]] over the first layer, [[and]]

a semiconductor layer over the gate insulating layer;

a wiring connected to at least one of a source and a drain; and

a ~~second~~ third layer including at least one of silicon nitride and ~~nitride oxide~~ silicon oxide formed [[to be]] on and in direct contact with the wiring,

wherein the wiring is formed by fusing conductive nanoparticles.

3. (Currently amended) A liquid crystal display device comprising:

a pair of substrates;

a liquid crystal interposed between the pair of substrates;

a first thin film transistor over one of the pair of substrates;

a pixel electrode connected to the first thin film transistor;

a driver circuit constructed by a second thin film transistor which comprises the same layer structure [[of]] as the first thin film transistor; and

a wiring extending from the driver circuit and connected to a gate electrode of the first thin film transistor,

wherein the first thin film transistor comprises:

the gate electrode formed over the one of the pair of substrates by fusing conductive nanoparticles,

a first layer including at least one of silicon nitride and ~~nitride oxide~~ silicon nitride oxide formed on and in direct contact with the gate electrode,

a gate insulating layer at least ~~containing~~ comprising a second layer ~~comprising~~ including silicon oxide over the first layer, and

a semiconductor layer over the gate insulating layer.

4. (Currently amended) A liquid crystal display device comprising:

a pair of substrates;

a liquid crystal interposed between the pair of substrates;

a first thin film transistor over one of the pair of substrates;

a pixel electrode connected to the first thin film transistor;

a driver circuit constructed by a second thin film transistor which comprises the same layer structure [[of]] as the first thin film transistor; and

a first wiring extending from the driver circuit and connected to a gate electrode of the first thin film transistor,

wherein the first thin film transistor comprises:

the gate electrode formed over the one of the pair of substrates by fusing conductive nanoparticles,

a first layer including at least one of silicon nitride and ~~nitride oxide~~ silicon nitride oxide formed on and in direct contact with the gate electrode,

a gate insulating layer at least ~~containing~~ comprising a second layer including silicon oxide [[layer]] over the first layer, [[and]]

a semiconductor layer over the gate insulating layer;

a second wiring connected to at least one of a source and a drain; and

a ~~second~~ third layer including at least one of silicon nitride and ~~nitride oxide~~ silicon oxide formed on and in direct contact with the second wiring,

wherein the second wiring is formed by fusing conductive nanoparticles.

5. (Original) The liquid crystal display device according to any one of claims 1 to 4, wherein the conductive nanoparticles comprise Ag.

6. (Original) The liquid crystal display device according to claim 2 or 4,

wherein the semiconductor layer comprises at least one of hydrogen and halogen; and

wherein the semiconductor layer is a semi-amorphous semiconductor having a crystal structure.

7. (Previously amended) The liquid crystal display device according to claim 3 or 4, wherein the driver circuit comprises only an n-channel type thin film transistor.

8. (Currently amended) The liquid crystal display device according to claim 1 or 2,

wherein ~~the thin film transistor comprises~~ the semiconductor layer ~~including~~ includes hydrogen and halogen ~~and which is a semiconductor having a crystal structure~~,

wherein the semiconductor layer has a crystal structure, and

wherein the thin film transistor is capable of being operated in electric field effect mobility of from 1 $cm^2/V \cdot sec$ to 15 $cm^2/V \cdot sec$.

9. (Currently amended) The liquid crystal display device according to claim 3 or 4,

wherein each of the semiconductor layer of the first thin film transistor and a semiconductor layer of the second thin film transistor ~~comprise the semiconductor layer including~~ includes hydrogen and halogen ~~and which is a semiconductor having a crystal structure~~,

wherein each of the semiconductor layer of the first thin film transistor and the semiconductor layer of the second thin film transistor has a crystal structure, and

wherein the first thin film transistor and the second thin film transistor are capable of being operated in electric field effect mobility of from 1 $cm^2/V \cdot sec$ to 15 $cm^2/V \cdot sec$.

10. (Original) A liquid crystal television receiver comprising the liquid crystal display device according to any one of claims 1 to 4.

11. (Currently amended) A method for manufacturing a liquid crystal display device comprising the steps of:

forming a gate electrode over a substrate having an insulating surface with a droplet discharge method using a composition containing conductive nanoparticles;

laminating a gate insulating layer, a semiconductor layer, and an insulating layer over the gate electrode;

forming a first mask in a position overlapping with the gate electrode with a droplet discharge method;

forming a channel protective layer by etching the insulating layer by using the first mask;

forming a semiconductor layer containing one conductivity type impurity;

forming a second mask in a region including the gate electrode with a droplet discharge method;

etching the semiconductor layer containing one conductivity type impurity and the semiconductor layer by using the second mask;

forming source and drain wirings with a droplet discharge method; and

etching the semiconductor layer containing one conductivity type impurity over the channel protective layer by using the source and drain wirings as masks.

12. (Currently amended) A method for manufacturing a liquid crystal display device comprising the steps of:

forming a gate electrode and a connection wiring over a substrate having an insulating surface with a droplet discharge method using a composition containing conductive nanoparticles;

laminating a gate insulating layer, a semiconductor layer, and an insulating layer over the gate electrode;

forming a first mask in a position overlapping with the gate electrode with a droplet discharge method;

forming a channel protective layer by etching the insulating layer by using the first mask;

forming a semiconductor layer containing one conductivity type impurity;

forming a second mask in a region including the gate electrode with a droplet discharge method;

etching the semiconductor layer containing one conductivity type impurity and the semiconductor layer by using the second mask;

partially exposing the connection wiring by selectively etching the gate insulating layer;

forming a source wiring and a drain wiring and connecting at least one of the source wiring and the drain wiring to the connection wiring at the same time; and

etching the semiconductor layer containing one conductivity type impurity over the channel protective layer by using the source and drain wirings as masks.

13. (Previously amended) The method for manufacturing a liquid crystal display device according to claim 11 or 12, wherein the step of laminating the gate insulating layer, the semiconductor layer, and the insulating layer over the gate electrode is carried out without exposing to the atmosphere.

14. (Currently amended) The method for manufacturing a liquid crystal display device according to claim 11 or 12, wherein the gate insulating layer is ~~sequentially~~

~~laminated by~~ formed by sequentially laminating a first silicon nitride film, a silicon oxide film, and a second silicon nitride film.

15. (New) The method for manufacturing a liquid crystal display device according to claim 11 or 12, wherein average particle size of the conductive nanoparticles is from 5 nm to 10 nm.

16. (New) The method for manufacturing a liquid crystal display device according to claim 11 or 12, wherein the first mask is formed using a composition containing conductive nanoparticles.

17. (New) The method for manufacturing a liquid crystal display device according to claim 11 or 12, wherein the second mask is formed using a composition containing conductive nanoparticles.

18. (New) The method for manufacturing a liquid crystal display device according to claim 11, wherein the source and drain wirings are formed using a composition containing conductive nanoparticles.